ABSTRACT

When exposing a same resist layer of a wafer ~~W (W1 (or W2)~~ a plurality of times, at least in one exposure of the plurality of exposures, by filling a space between a projection optical system, which projects an exposure light ~~(IL)~~ on the wafer ~~(W1 (or W2))~~, and the wafer with water by a liquid supply/drainage unit, a substantial wavelength of exposure light ~~(IL)~~ that reaches the wafer is made to differ from a substantial wavelength of exposure light ~~(IL)~~ in another exposure. Accordingly, exposure with high precision and high throughput can be achieved.